# 2.5V Drive Nch+Nch MOS FET **US6K1**

### Structure

Silicon N-channel MOS FET

### Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT6).
- 3) Low voltage drive (2.5V drive).

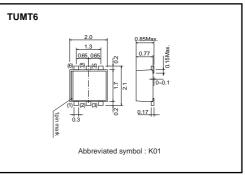
### Applications

Switching

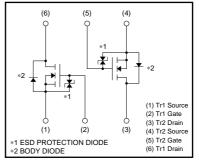
### Packaging specifications

	Package	Taping	
Туре	Code	TR	
	Basic ordering unit (pieces)	3000	
US6K1		0	

### •External dimensions (Unit : mm)



### Inner circuit



### ●Absolute maximum ratings (Ta=25°C)

	Symbol	Limits	Unit
	V <sub>DSS</sub>	30	V
	V <sub>GSS</sub>	12	V
Continuous	ID	±1.5	А
Pulsed	I <sub>DP</sub> *1	±6	А
Continuous	ls	0.6	А
Pulsed	lsp *1	6	А
Total power dissipation		1.0	W / TOTAL
		0.7	W / ELEMENT
Channel temperature		150	°C
Range of storage temperature		-55 to +150	°C
	Pulsed Continuous Pulsed	VDSS   VGSS   Continuous   Pulsed   IDP   Pulsed   ISP   Pulsed   ISP   Pulsed   ISP   Pulsed   ISP   Pulsed   ISP   Tch	VDSS 30   VGSS 12   Continuous Ib ±1.5   Pulsed IbP *1 ±6   Continuous Is 0.6   Pulsed IsP *1 6   Pulsed IsP *1 6   PD *2 1.0   0.7 Tch 150

\*1 Pw≤10µs, Duty cycle≤1% \*2 Mounted on a ceramic board

### Thermal resistance

Symbol	Limits	Unit
Ptb(cb, c)*	125	°C/W / TOTAL
Kiii(Cii-a)	179	°C/W / ELEMENT
	Symbol Rth(ch-a)*	Rth(ch-a)* 125

\* Mounted on a ceramic board



# US6K1

## Transistors

### •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	lgss	-	-	10	μΑ	Vgs=12V, Vds=0V	
Drain-source breakdown voltage	V(BR) DSS	30	-	-	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V	
Zero gate voltage drain current	IDSS	-	-	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V	
Gate threshold voltage	VGS (th)	0.5	-	1.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	
Static drain-source on-state resistance	R <sub>DS</sub> (on)*	-	170	240	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 4.5V	
		-	180	250	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 4.0V	
		-	240	340	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 2.5V	
Forward transfer admittance	Y <sub>fs</sub> *	1.5	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1.5A	
Input capacitance	Ciss	-	80	_	pF	V <sub>DS</sub> = 10V	
Output capacitance	Coss	-	13	-	рF	V <sub>GS</sub> =0V	
Reverse transfer capacitance	Crss	-	12	-	рF	f=1MHz	
Turn-on delay time	td (on) *	-	7	-	ns	Vdd≒ 15V	
Rise time	tr *	-	9	_	ns	$I_{D}=0.75A$	
Turn-off delay time	td (off) *	-	15	-	ns	Vgs= 4.5V RL= 20Ω	
Fall time	t <sub>f</sub> *	-	6	-	ns	$R_G = 10\Omega$	
Total gate charge	Qg *	-	1.6	2.2	nC	V <sub>DD</sub> ≒15V	
Gate-source charge	Q <sub>gs</sub> *	-	0.5	-	nC	V <sub>GS</sub> = 4.5V	
Gate-drain charge	Q <sub>gd</sub> *	-	0.3	-	nC	I <sub>D</sub> = 1.5A	

### •Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	1.2	V	Is= 0.6A, V <sub>GS</sub> =0V

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